



N-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^d	Q_g (Typ.)
40	0.040 at $V_{GS} = 10$ V	5.2	8
	0.045 at $V_{GS} = 4.5$ V	4.9	

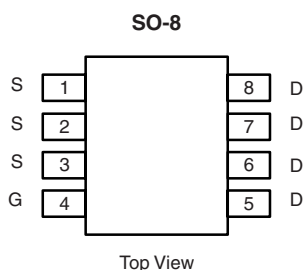
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g
- 100 % R_g UIS Tested

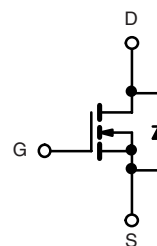
RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- CCFL Inverter



Ordering Information: Si4446DY-T1-E3 (Lead (Pb)-free)
Si4446DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	40		V
Gate-Source Voltage		V_{GS}	± 12		
Continuous Drain Current ($T_J = 150$ °C) ^a	$T_A = 25$ °C	I_D	5.2	3.9	A
	$T_A = 70$ °C		4.2	3.1	
Pulsed Drain Current		I_{DM}	30		
Continuous Source Current (Diode Conduction) ^a		I_S	1.7	0.9	
Avalanche Current	$L = 0.1$ mH	I_{AS}	13		mJ
		E_{AS}	8.5		
Maximum Power Dissipation ^a	$T_A = 25$ °C	P_D	2.0	1.1	W
	$T_A = 70$ °C		1.3	0.7	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ s	R_{thJA}	52	62.5	°C/W
	Steady State		90	110	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	32	40	

Notes:

a. Surface mounted on 1" x 1" FR4 board.



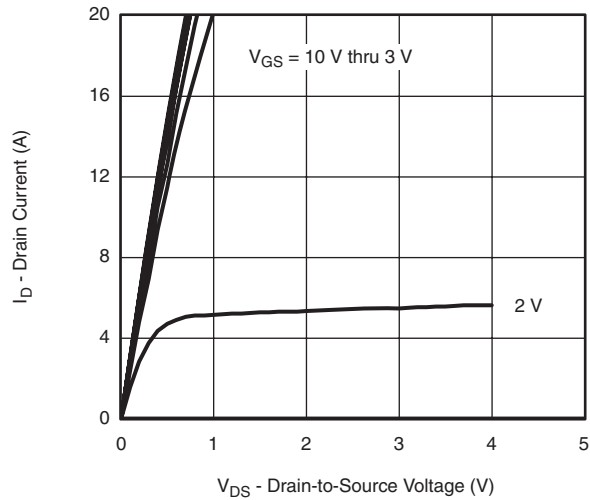
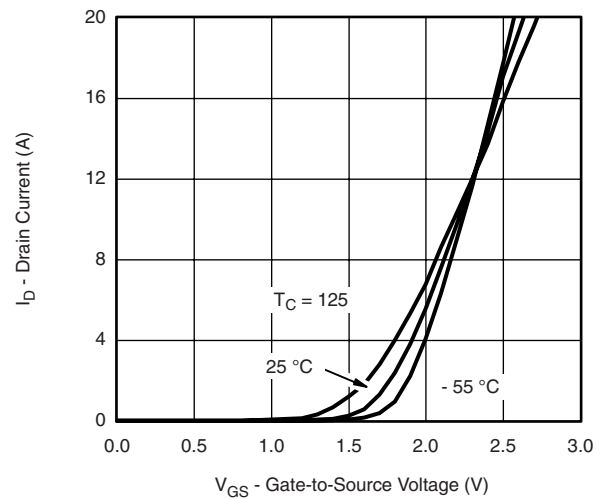
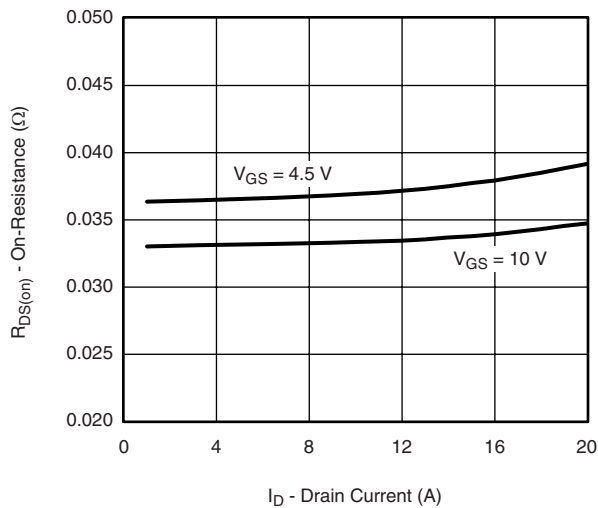
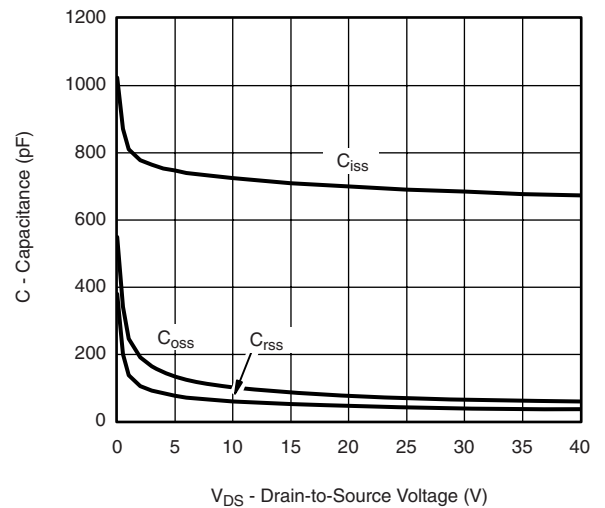
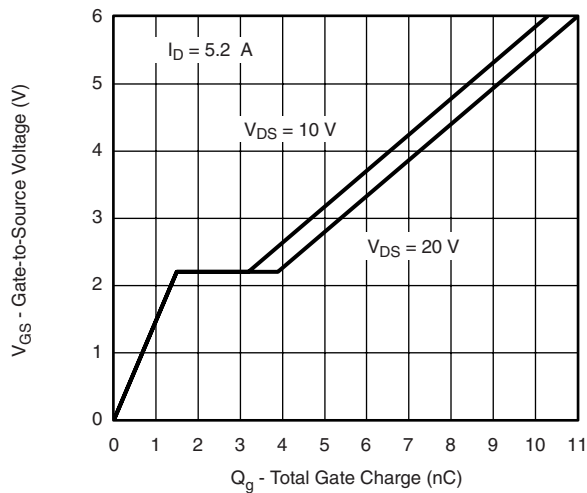
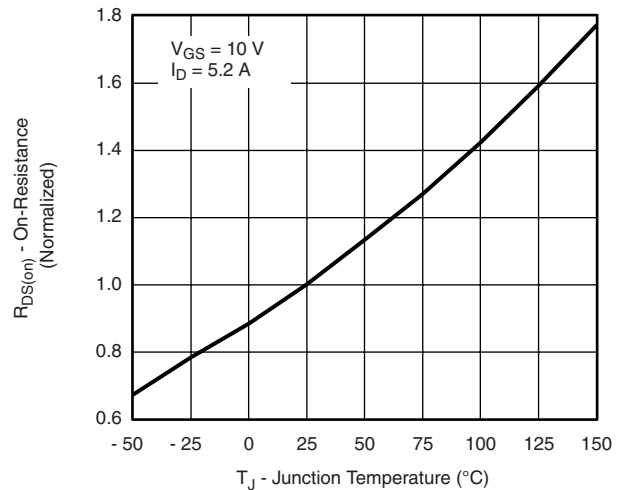
SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	0.6		1.6	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		40		$\text{mV}/^{\circ}\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 3.8		
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 12\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 40\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 40\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 55\text{ }^{\circ}\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$, $V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 5.2\text{ A}$		0.033	0.040	Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 4.9\text{ A}$		0.037	0.045	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}$, $I_D = 5.2\text{ A}$		18		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 1.7\text{ A}$, $V_{GS} = 0\text{ V}$		0.75	1.2	V
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 20\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		700		pF
Output Capacitance	C_{oss}			76		
Reverse Transfer Capacitance	C_{rss}			45		
Total Gate Charge	Q_g	$V_{DS} = 20\text{ V}$, $V_{GS} = 4.5\text{ V}$, $I_D = 5.2\text{ A}$		8	12	nC
Gate-Source Charge	Q_{gs}			1.5		
Gate-Drain Charge	Q_{gd}			2.4		
Gate Resistance	R_g	$f = 1\text{ MHz}$		1.9	2.9	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}$, $R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 6\text{ }\Omega$		7	11	ns
Rise Time	t_r			11	17	
Turn-Off Delay Time	$t_{d(off)}$			27	40	
Fall Time	t_f			8	13	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 1.7\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}$		25	40	nC
Body Diode Reverse Recovery Charge	Q_{rr}			17	26	

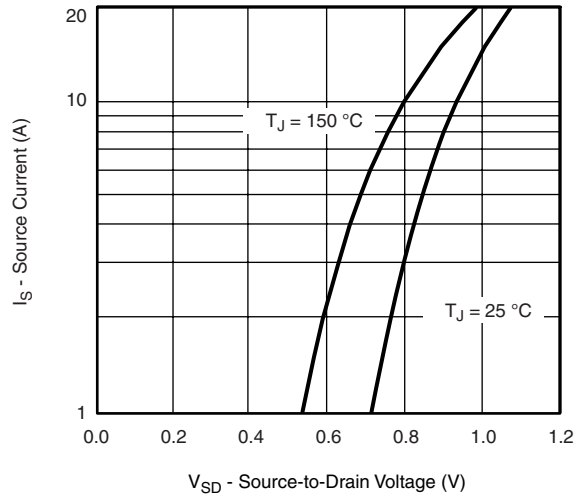
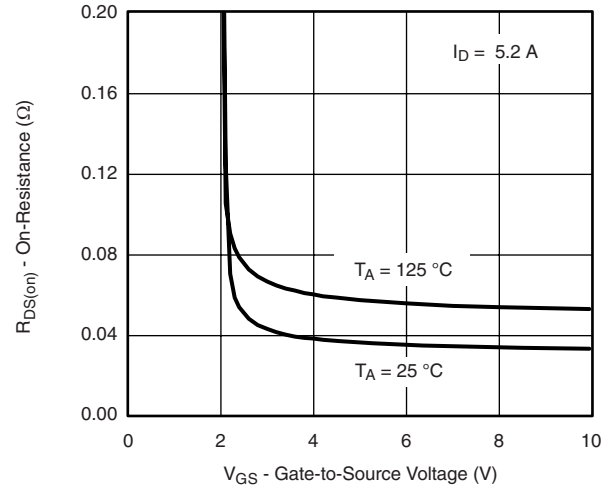
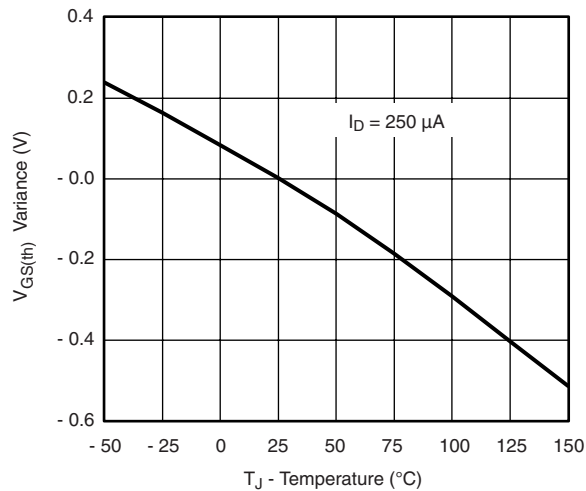
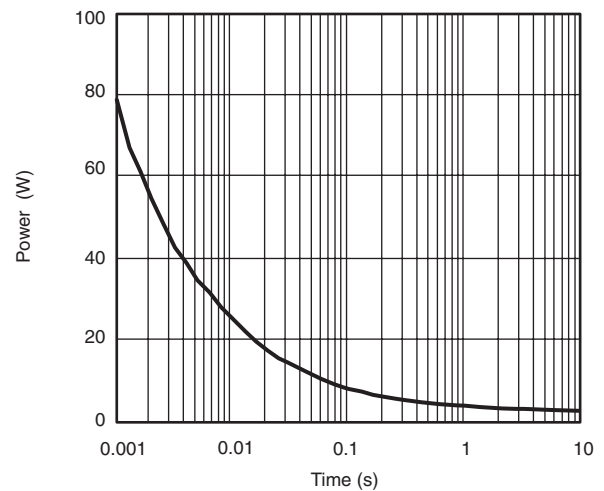
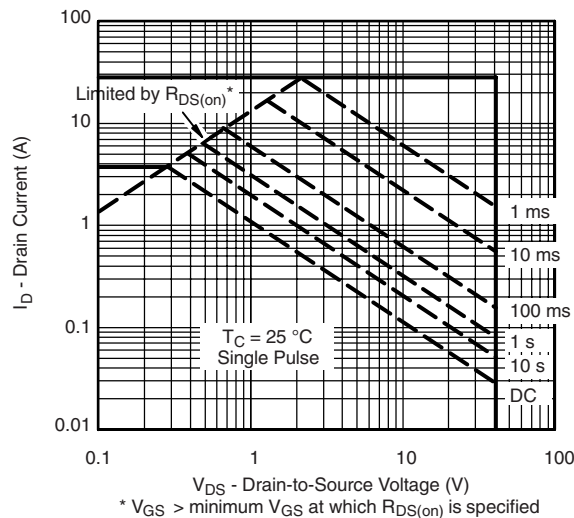
Notes:

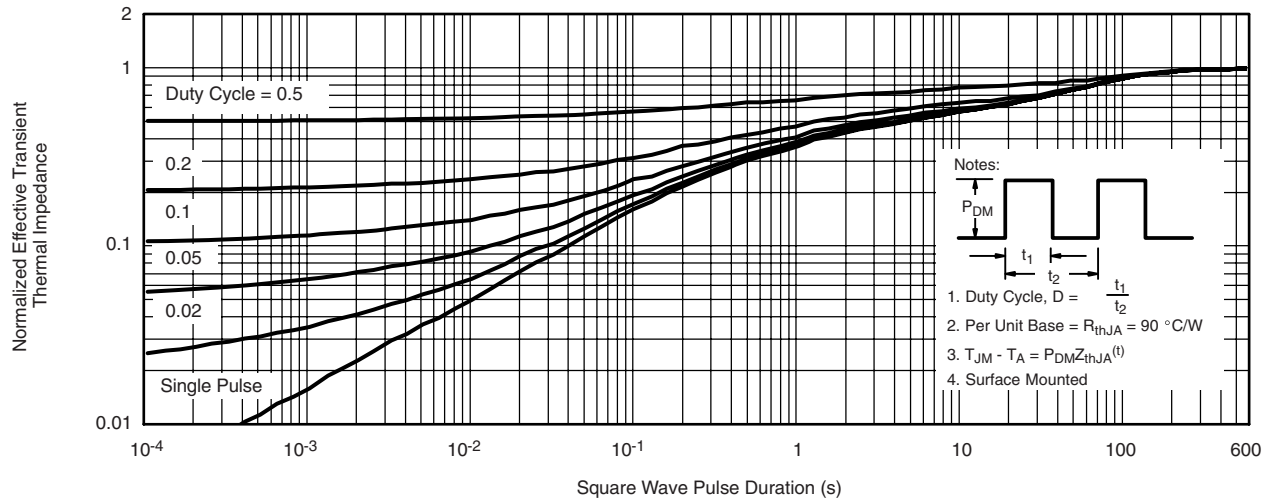
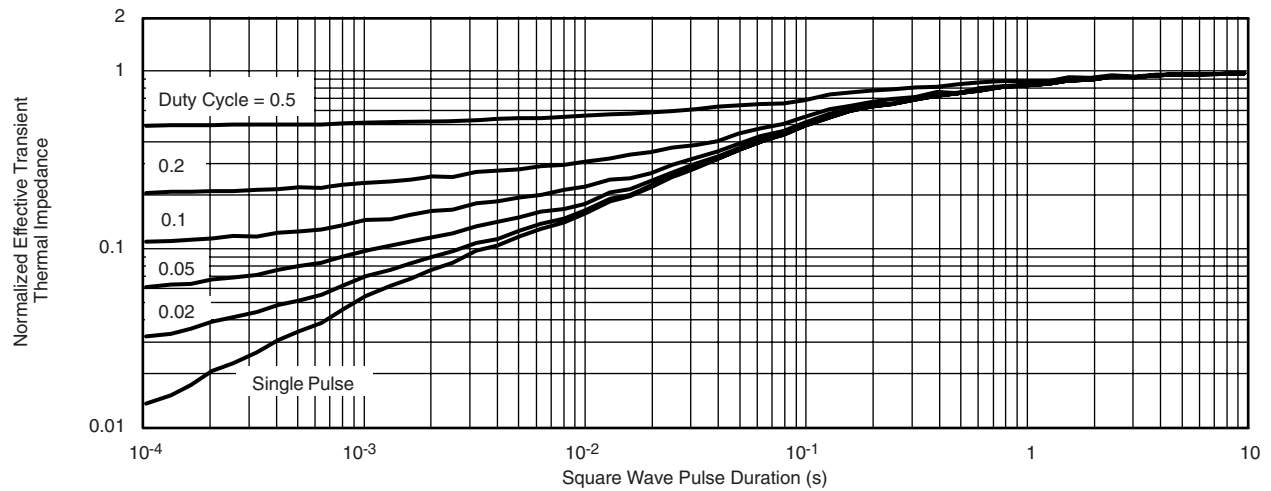
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power, Junction-to-Ambient****Safe Operating Area**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot**

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